

United States Patent [19]

Ogawa

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[54] **PATTERN FORMING METHOD**

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[30] **Foreign Application Priority Data**

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[58] Field of Search **427/43.1, 44, 54.1; 156/655, 657, 659.1, 643**

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[57] **ABSTRACT**

Method of forming any film pattern on an arbitrary substrate, more particularly, a pattern forming method which comprises selectively forming a film on an arbitrary substrate, by use of chemical vapor reaction, and further, a method of forming the pattern of an organic film by selectively removing the organic film at a lower layer, using the pattern of the Langmuir-Blodgett's film or chemical adsorption film containing Si as a mask.

10 Claims, 10 Drawing Figures

